

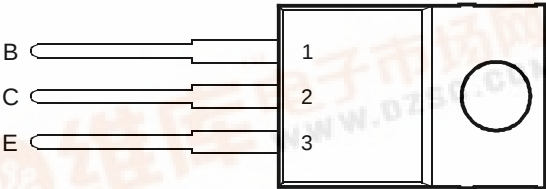
BD895A, BD897A, BD899A
NPN SILICON POWER DARLINGTONS

Copyright © 1997, Power Innovations Limited, UK

AUGUST 1993 - REVISED MARCH 1997

- **Designed for Complementary Use with BD896A, BD898A and BD900A**
- **70 W at 25°C Case Temperature**
- **8 A Continuous Collector Current**
- **Minimum h_{FE} of 750 at 3V, 3A**

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BD895A	V_{CBO}	45	V
	BD897A		60	
	BD899A		80	
Collector-emitter voltage ($I_B = 0$)	BD895A	V_{CEO}	45	V
	BD897A		60	
	BD899A		80	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	8	A
Continuous base current		I_B	0.3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)		P_{tot}	70	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)		P_{tot}	2	W
Operating free-air temperature range		T_A	-65 to +150	°C
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.
2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.



BD895A, BD897A, BD899A

NPN SILICON POWER DARLINGTONS

AUGUST 1993 - REVISED MARCH 1997

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 100 \text{ mA}$ $I_B = 0$ (see Note 3) BD895A BD897A BD899A	45 60 80			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$ $I_B = 0$ BD895A $V_{CE} = 30 \text{ V}$ $I_B = 0$ BD897A $V_{CE} = 40 \text{ V}$ $I_B = 0$ BD899A			0.5 0.5 0.5	mA
I_{CBO} Collector cut-off current	$V_{CB} = 45 \text{ V}$ $I_E = 0$ BD895A $V_{CB} = 60 \text{ V}$ $I_E = 0$ BD897A $V_{CB} = 80 \text{ V}$ $I_E = 0$ BD899A $V_{CB} = 45 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$ BD895A $V_{CB} = 60 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$ BD897A $V_{CB} = 80 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$ BD899A			0.2 0.2 0.2 2 2 2	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$ $I_C = 0$ (see Notes 3 and 4)			2	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 3 \text{ V}$ $I_C = 4 \text{ A}$ (see Notes 3 and 4)	750			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 16 \text{ mA}$ $I_C = 4 \text{ A}$ (see Notes 3 and 4)			2.8	V
$V_{BE(on)}$ Base-emitter voltage	$V_{CE} = 3 \text{ V}$ $I_C = 4 \text{ A}$ (see Notes 3 and 4)			2.5	V
V_{EC} Parallel diode forward voltage	$I_E = 8 \text{ A}$ $I_B = 0$			3.5	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.79	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]	MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 3 \text{ A}$ $I_{B(on)} = 12 \text{ mA}$ $I_{B(off)} = -12 \text{ mA}$		1		μs
t_{off} Turn-off time	$V_{BE(off)} = -3.5 \text{ V}$ $R_L = 10 \Omega$ $t_p = 20 \mu\text{s}$, $dc \leq 2\%$		5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

BD895A, BD897A, BD899A NPN SILICON POWER DARLINGTONS

AUGUST 1993 - REVISED MARCH 1997

TYPICAL CHARACTERISTICS

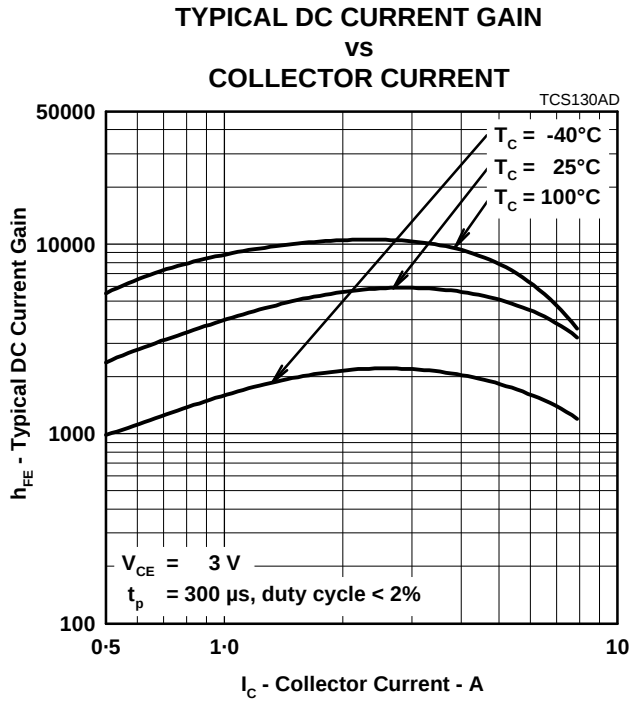


Figure 1.

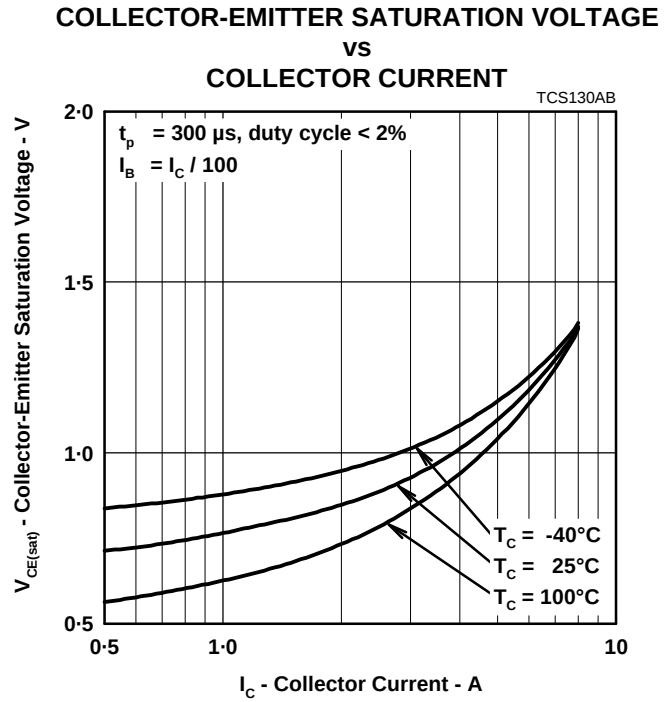


Figure 2.

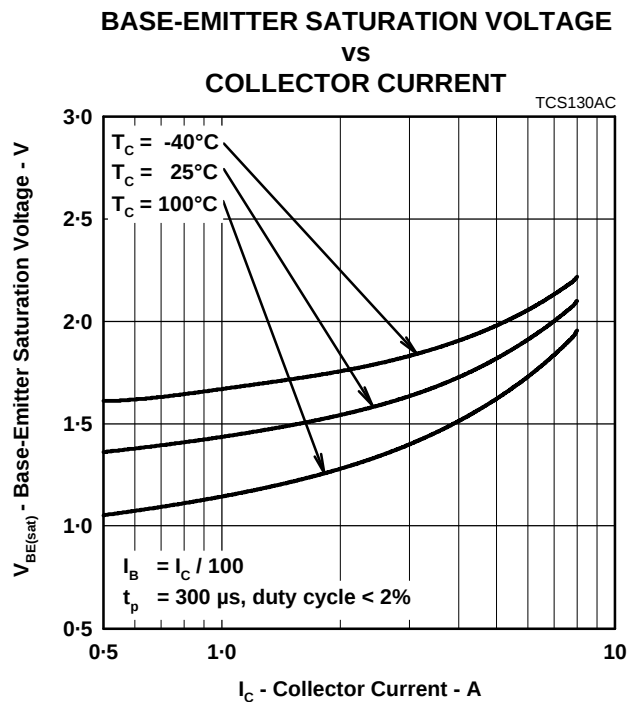


Figure 3.

BD895A, BD897A, BD899A
NPN SILICON POWER DARLINGTONS

AUGUST 1993 - REVISED MARCH 1997

MAXIMUM SAFE OPERATING REGIONS

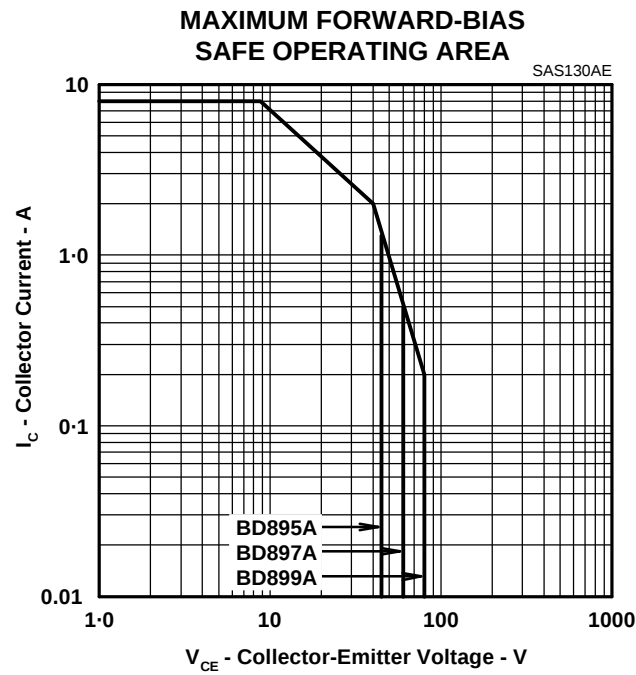


Figure 4.

THERMAL INFORMATION

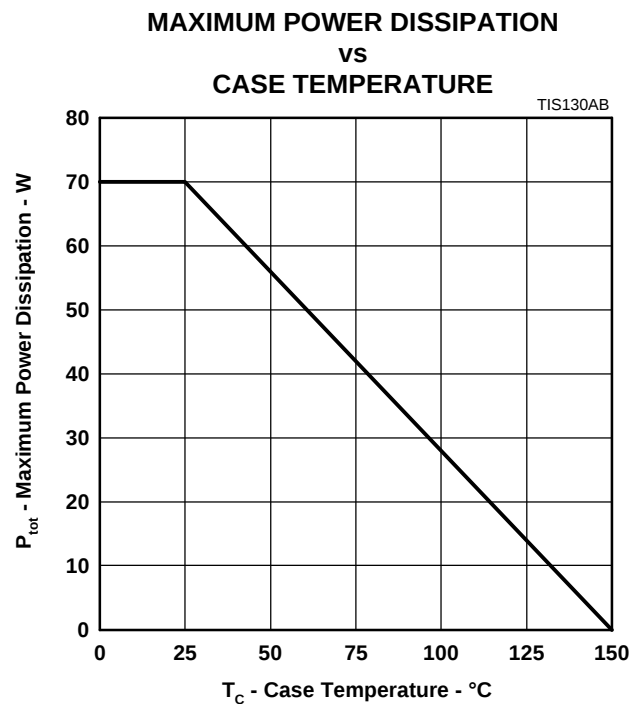


Figure 5.

BD895A, BD897A, BD899A NPN SILICON POWER DARLINGTONS

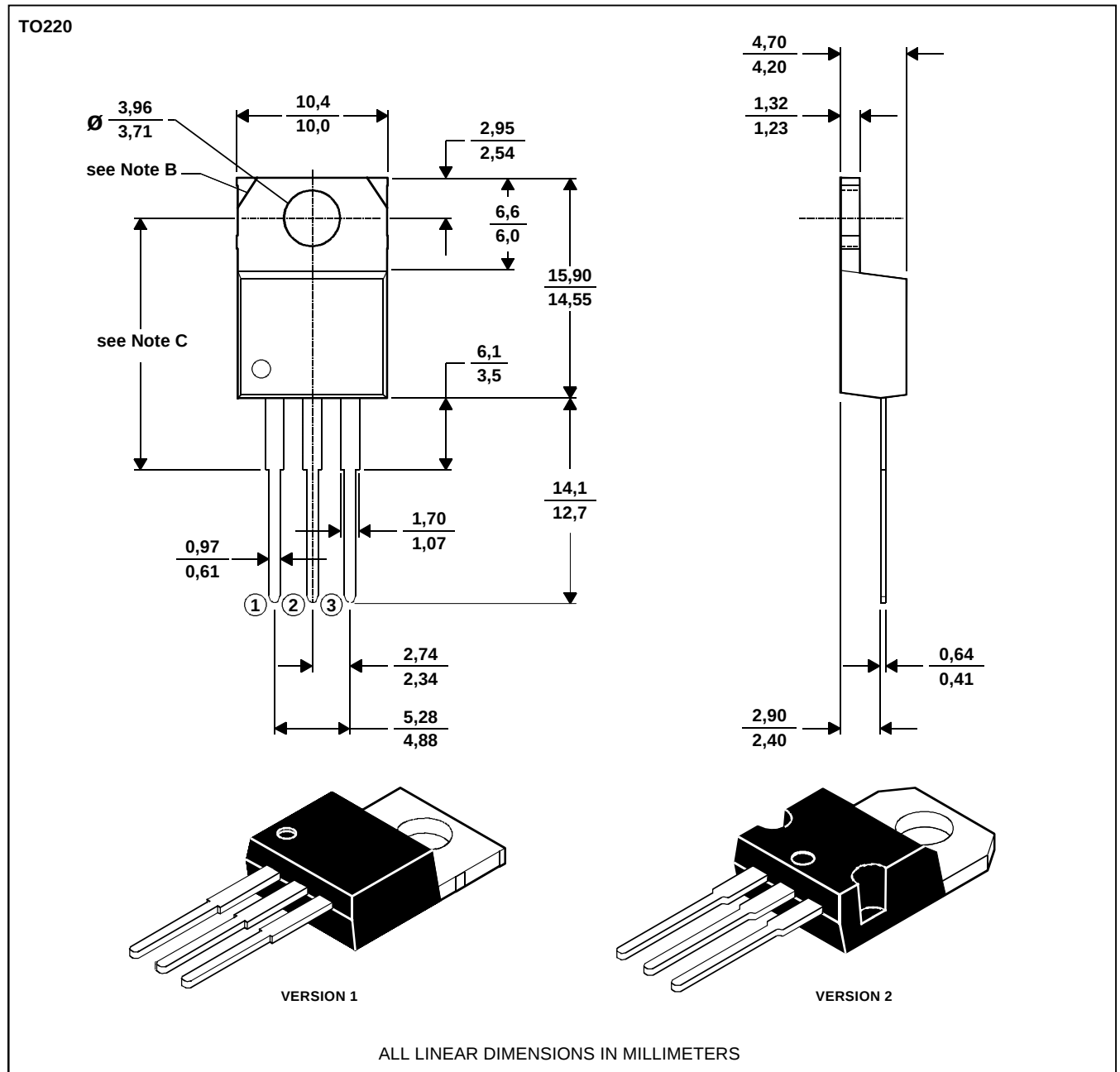
AUGUST 1993 - REVISED MARCH 1997

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



- NOTES: A. The centre pin is in electrical contact with the mounting tab.
B. Mounting tab corner profile according to package version.
C. Typical fixing hole centre stand off height according to package version.
Version 1, 18.0 mm. Version 2, 17.6 mm.

MDXXBE

BD895A, BD897A, BD899A

NPN SILICON POWER DARLINGTONS

AUGUST 1993 - REVISED MARCH 1997

IMPORTANT NOTICE

Power Innovations Limited (PI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to verify, before placing orders, that the information being relied on is current.

PI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with PI's standard warranty. Testing and other quality control techniques are utilized to the extent PI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except as mandated by government requirements.

PI accepts no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor is any license, either express or implied, granted under any patent right, copyright, design right, or other intellectual property right of PI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

PI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS.

Copyright © 1997, Power Innovations Limited